

N-channel TrenchMOS standard level FET

Rev. 2 — 2 February 2011

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

	Guick reference ua					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	75	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	53	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	138	W
Static cha	racteristics					
R _{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 175 \ ^{\circ}\text{C}; \text{ see } \underline{\text{Figure 12}}; \\ \text{see } \underline{\text{Figure 13}} \end{array}$	-	-	49	mΩ
		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \ ^{\circ}\text{C}; \text{ see } \underline{\text{Figure 12}}; \\ \text{see } \underline{\text{Figure 13}} \end{array}$	-	17	23	mΩ
Avalanche	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 49 \text{ A}; \text{V}_{\text{sup}} \leq 75 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 10 \text{ V}; \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	-	120	mJ

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BUK7623-75A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	75	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \ k\Omega$	-	75	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	53	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	37	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>	-	213	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	138	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	-	53	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	213	А
Avalanche rug	ggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 49 \; A; \; V_{sup} \leq 75 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(\text{init})} = 25 \; ^\circ \text{C}; \; \text{unclamped} \end{array}$	-	120	mJ

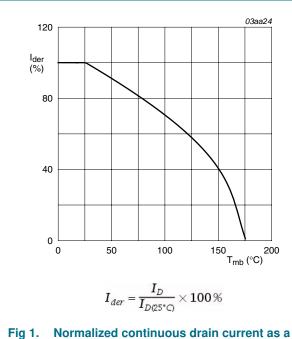


Fig 1. Normalized continuous drain current as a function of mounting base temperature

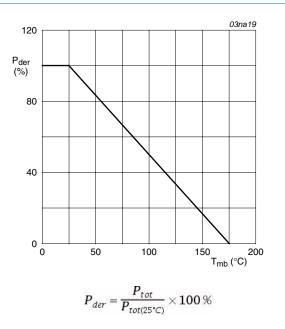
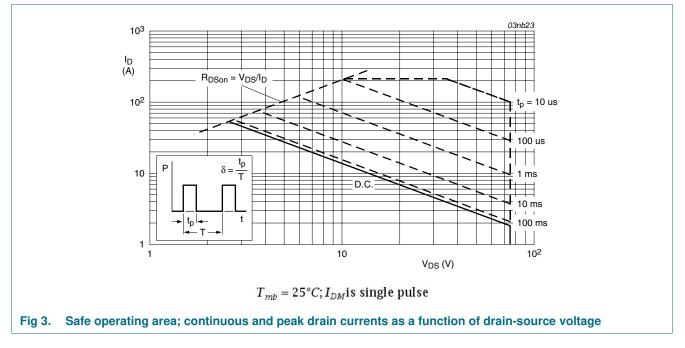


Fig 2. Normalized total power dissipation as a function of mounting base temperature

BUK7623-75A

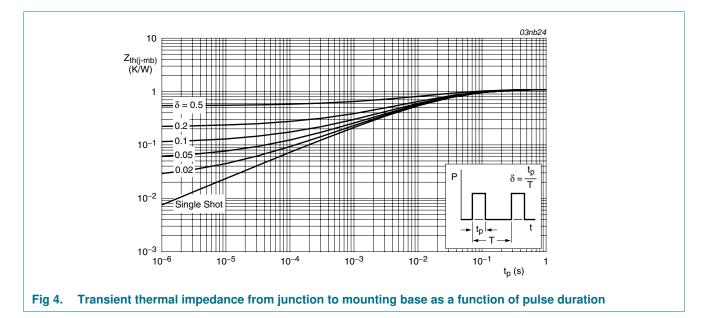
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



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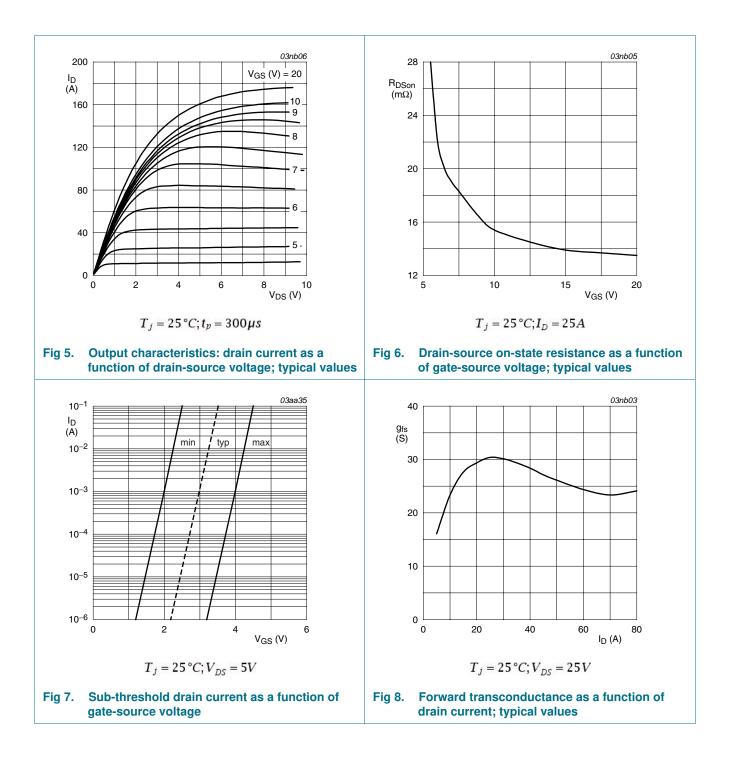
Characteristics 6.

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source breakdown voltage		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	75	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	70	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 11</u>	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 11</u>	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_{j} = 25 ^{\circ}\text{C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	49	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	17	23	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1789	2385	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	382	458	pF
C _{rss}	reverse transfer capacitance		-	219	300	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	14	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	66	-	ns
t _{d(off)}	turn-off delay time		-	61	-	ns
t _f	fall time		-	41	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die; T _j = 25 °C	-	2.5	-	nH
L _S	internal source inductance	from source lead to source bond pad	-	7.5	-	nH
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 46 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	53	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	144	-	nC

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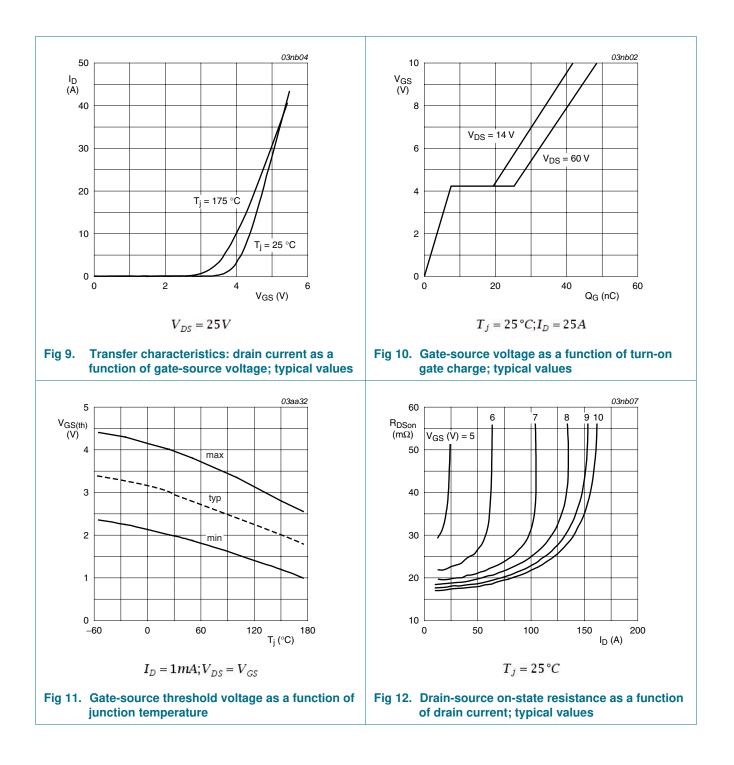
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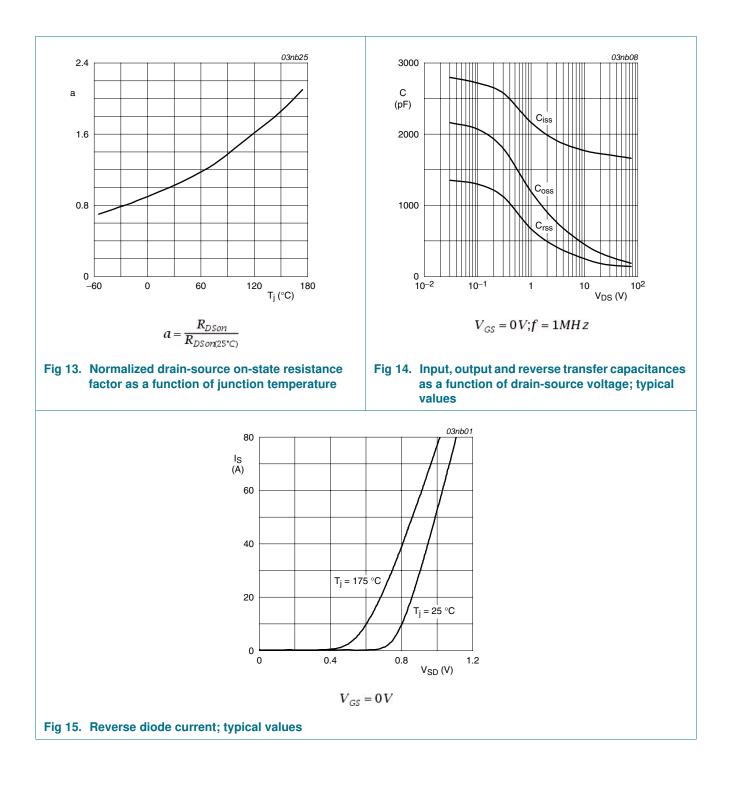
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7. Package outline

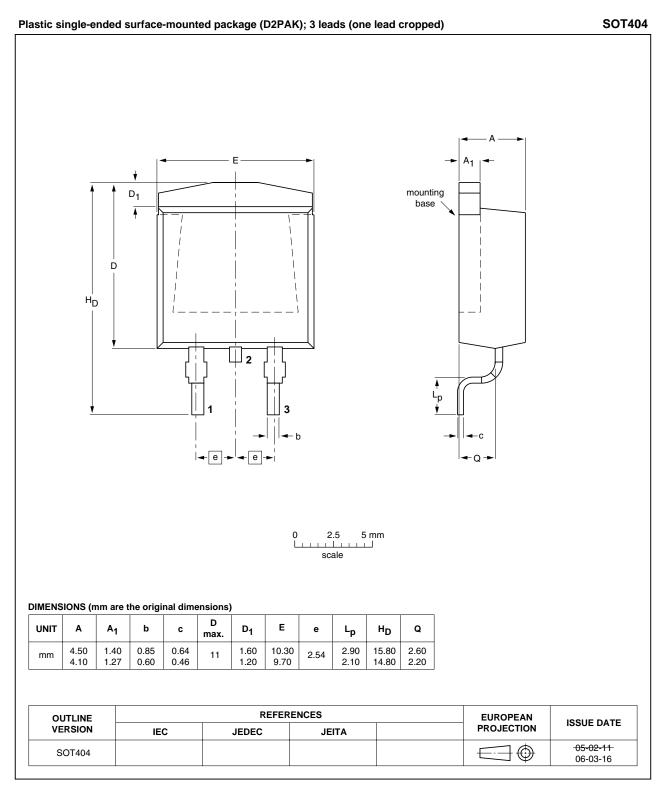


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision histo	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7623-75A	20110202	Product data sheet	-	BUK7523_7623_75A-01
Modifications:		of this data sheet has to find the second seco	•	comply with the new identity
	 Legal texts 	have been adapted to	he new company na	me where appropriate.
	 Type number 	per BUK7623-75A separ	ated from data shee	t BUK7523_7623_75A-01.
BUK7523_7623_75A-01	20001009	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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